MOSFET – Power, Single N-Channel
40 V, 7.1 mΩ, 48 A

Product Preview

NVTYS007N04C

ON Semiconductor®

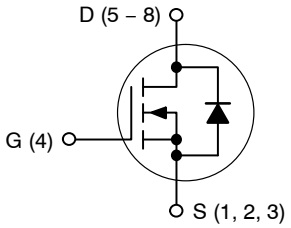
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Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	8.5 mΩ @ 10 V	48 A

N−Channel



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	40	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3, 4)	Steady State	T_C = 25°C	I_D	48	A
		T_C = 100°C		27	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2, 3)		T_C = 25°C	P_D	38	W
		T_C = 100°C		12	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	T_A = 25°C	I_D	14	A
		T_A = 100°C		10	
Power Dissipation $R_{\theta JA}$ (Notes 1, 3)		T_A = 25°C	P_D	3.1	W
		T_A = 100°C		1.5	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	193	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	31	A
Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 2.9 A)			E_{AS}	75	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

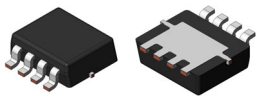
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State (Note 3)	$R_{\theta JC}$	4	°C/W
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	48.6	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51−12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface−mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.



LFPAK8
3.3x3.3
CASE 760AD

MARKING DIAGRAM



XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		40			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 40 V	T_J = 25°C			10	μA
			T_J = 125°C			250	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 30 μA		2.5		3.5	V
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15 A			7.1	8.5	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 15 A			29		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 25 V			625		pF
Output Capacitance	C_{oss}				335		
Reverse Transfer Capacitance	C_{rss}				15		
Threshold Gate Charge	$Q_{G(TH)}$	V_{GS} = 10 V, V_{DS} = 32 V, I_D = 15 A			2.2		nC
Gate−to−Source Charge	Q_{GS}				3.5		
Gate−to−Drain Charge	Q_{GD}				1.8		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 32 V, I_D = 15 A			10		nC
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 32 V, I_D = 15 A			9.5		ns
Rise Time	t_r				24		
Turn−Off Delay Time	$t_{d(off)}$				19		
Fall Time	t_f				6		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 15 A	T_J = 25°C		0.84	1.2	V
			T_J = 125°C		0.71		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 15 A			24		ns
Charge Time	t_a				11		
Discharge Time	t_b				12		
Reverse Recovery Charge	Q_{RR}				11		nC

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

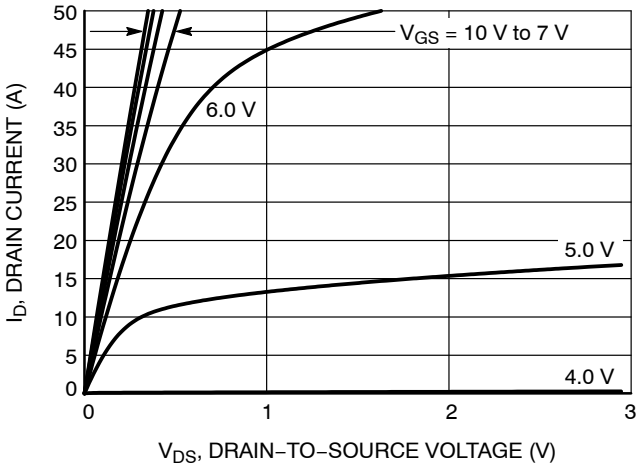


Figure 1. On−Region Characteristics

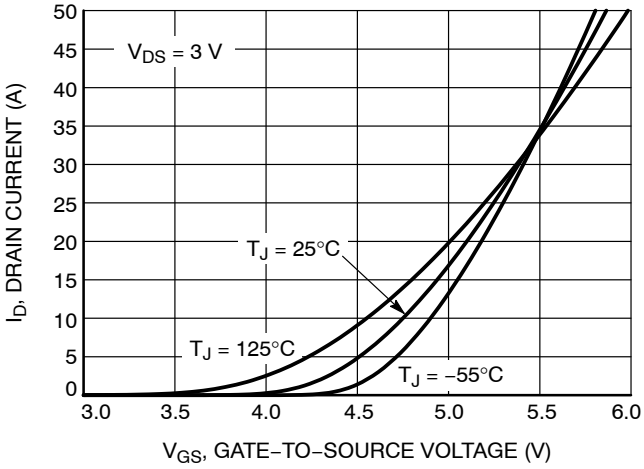


Figure 2. Transfer Characteristics

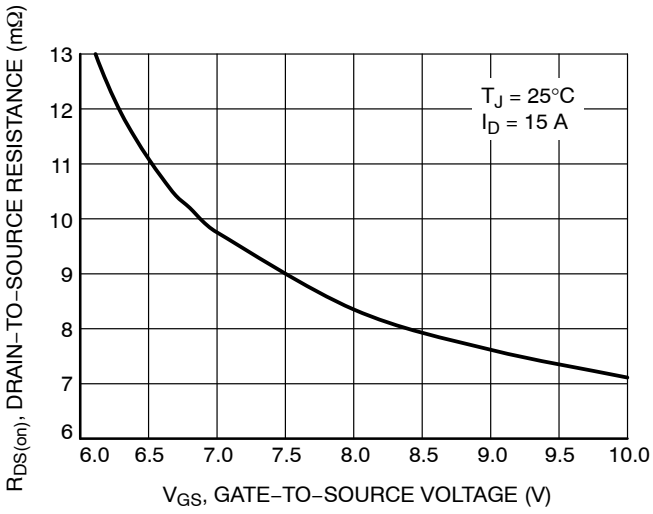


Figure 3. On−Resistance vs. Gate−to−Source Voltage

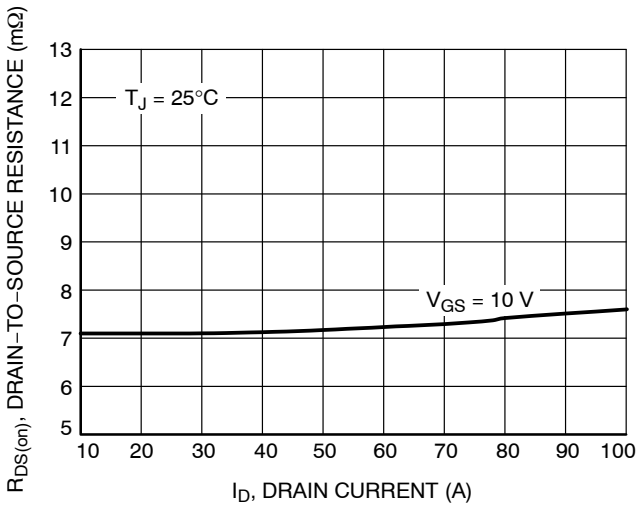


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

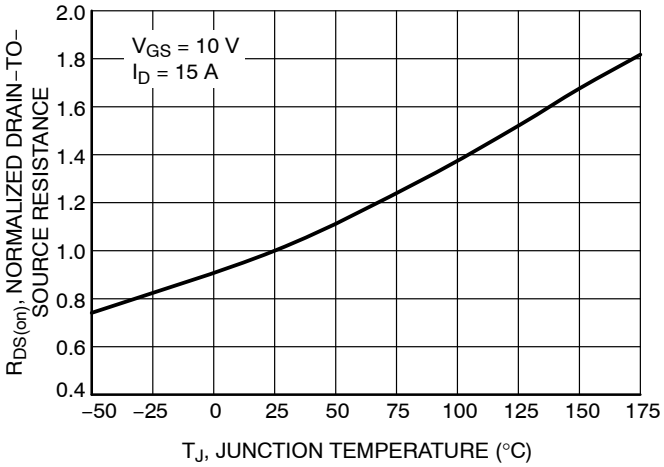


Figure 5. On−Resistance Variation with Temperature

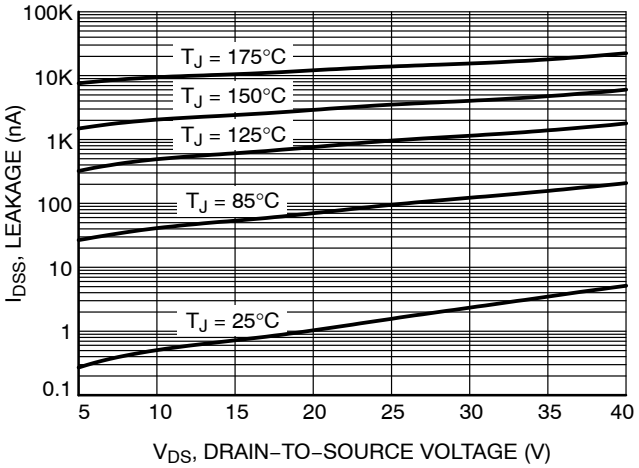


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

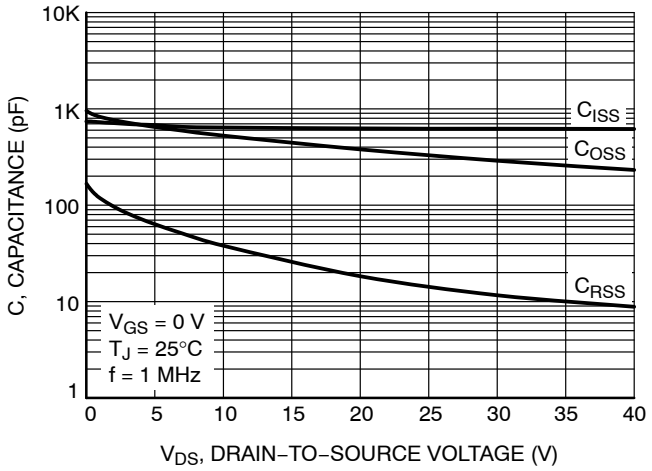


Figure 7. Capacitance Variation

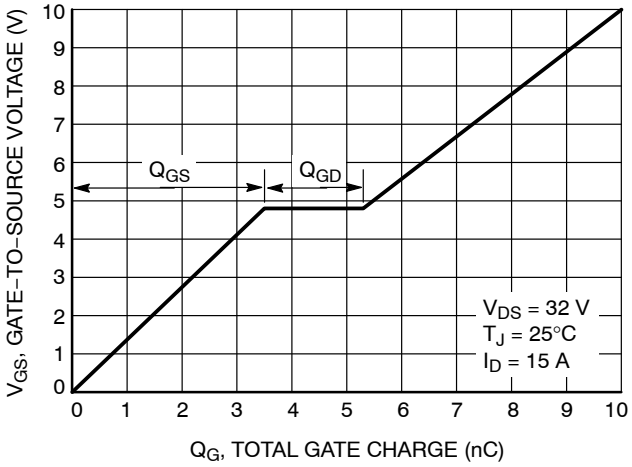


Figure 8. Gate−to−Source Voltage vs. Total Charge

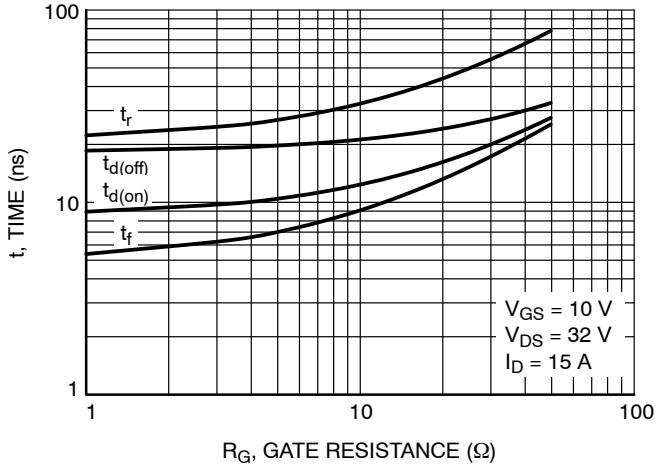


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

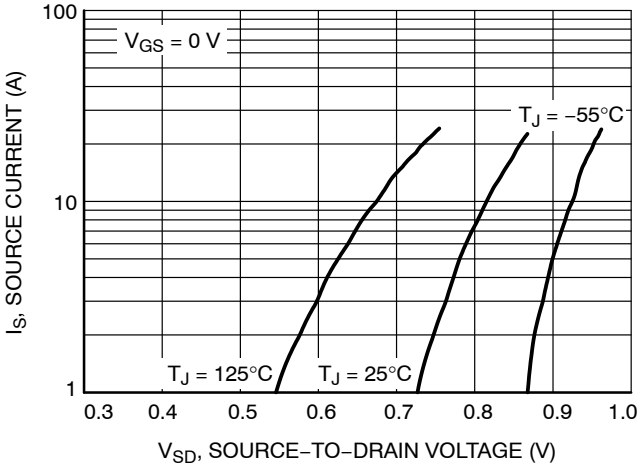


Figure 10. Diode Forward Voltage vs. Current

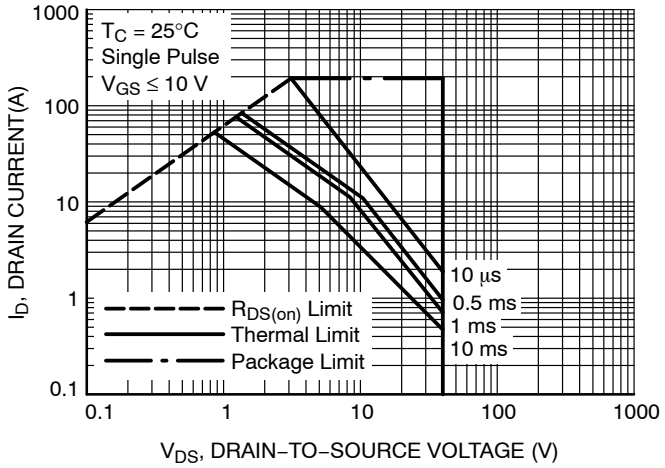


Figure 11. Maximum Rated Forward Biased Safe Operating Area

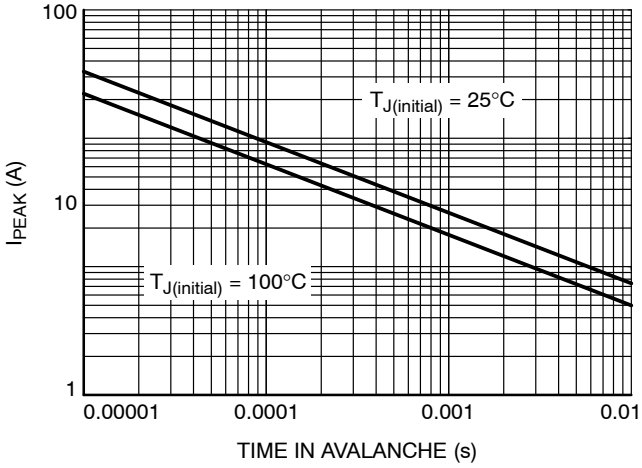


Figure 12. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS

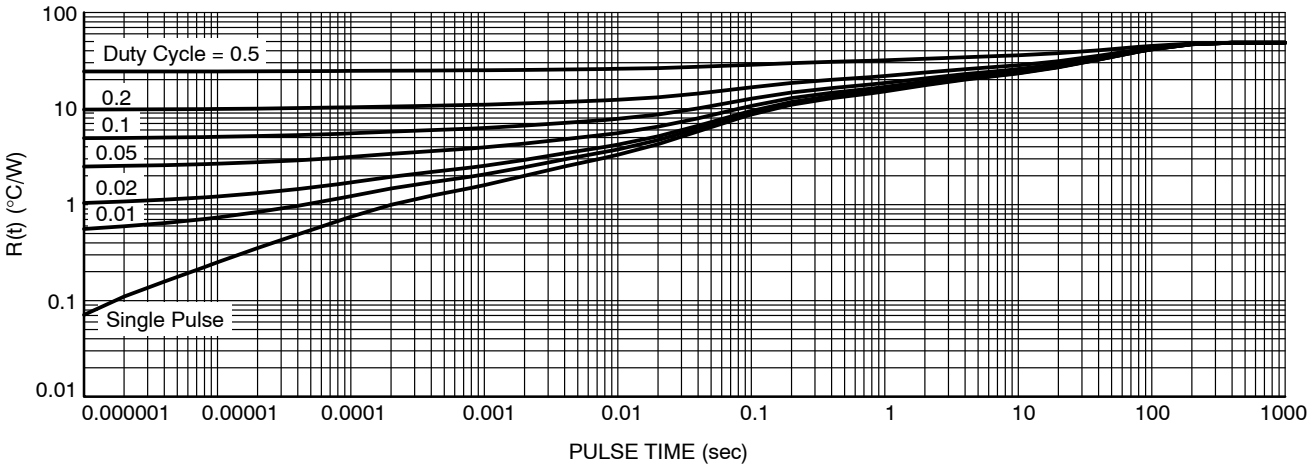


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

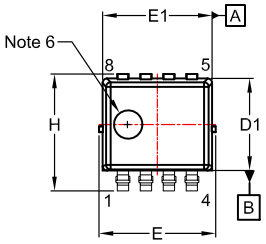
Device	Marking	Package	Shipping†
NVTYS007N04CTWG	TBD	LFPAK8 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

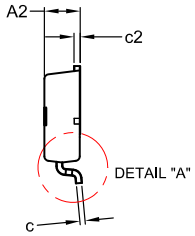
NVTYS007N04C

PACKAGE DIMENSIONS

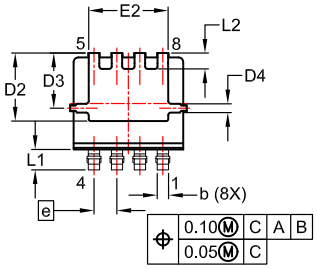
LFPAK8 3.3x3.3, 0.65P
CASE 760AD
ISSUE D



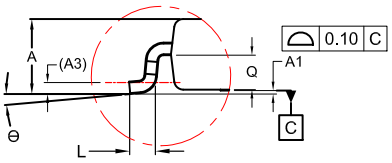
TOP VIEW



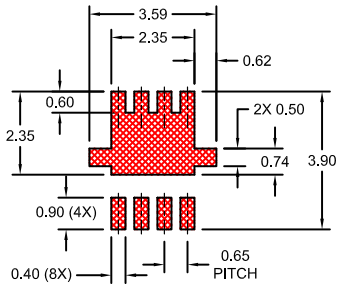
SIDE VIEW



BOTTOM VIEW



DETAIL 'A'
SCALE: 2:1



LAND PATTERN
RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS OR BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
6. OPTIONAL MOLD FEATURE.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.95	1.05	1.15
A1	0.00	0.05	0.10
A2	0.95	1.00	1.05
A3	0.15 REF		
b	0.27	0.32	0.37
c	0.12	0.17	0.22
c2	0.12	0.17	0.22
D1	2.50	2.60	2.70
D2	1.82	1.92	2.02
D3	1.46	1.56	1.66
D4	0.20	0.25	0.30
E	3.20	3.30	3.40
E1	3.00	3.10	3.20
E2	2.15	2.25	2.35
e	0.65 BSC		
H	3.20	3.30	3.40
L	0.25	0.37	0.50
L1	0.48	0.58	0.68
L2	0.35	0.45	0.55
Q	0.45	0.50	0.55
θ	0°	4°	8°

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